

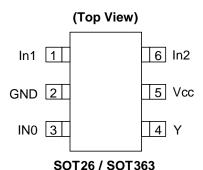
#### **Description**

The 74LVC1G97 is a single 3-input positive configurable multiple function gate with a standard totem pole output. The output state is determined by eight patterns of 3-bit input. The user can chose the logic functions MUX, AND, OR, NAND, NOR, inverter or non-inverting buffer. All inputs can be connected to ground or Vcc as required. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down. The user is reminded that the device can simulate several types of logic gates but may respond differently due to the Schmitt action at the inputs.

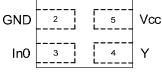
#### **Features**

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
  - o 200-V Machine Model (A115-A)
  - o 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- SOT26, SOT363, and DFN1010: Available in "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

#### **Pin Assignments**



(Top View)



DFN1010

#### **Applications**

- Voltage Level Shifting
- · General Purpose Logic
- Power Down Signal Isolation
- Wide array of products such as:
  - o PCs, networking, notebooks, netbooks, PDAs
  - o Computer peripherals, hard drives, CD/DVD ROM
  - o TV, DVD, DVR, set top box
  - o Cell Phones, Personal Navigation / GPS
  - o MP3 players ,Cameras, Video Recorders

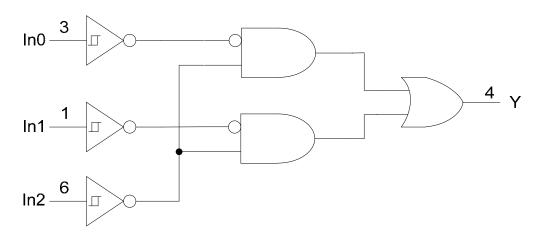
Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead\_free.html.



## **Pin Descriptions**

Pin Name	Description				
ln1	Data Input				
GND	Ground				
In0	Data Input				
Y	Data Output				
Vcc	Supply Voltage				
ln2	Data Input				

## **Logic Diagram**

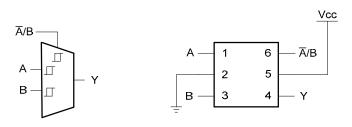


### **Function Table**

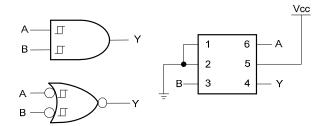
	Inputs		Output
ln2	ln1	In0	Υ
L	L	L	L
L	L	Н	L
L	Н	L	Н
L	Н	Н	Н
Н	L	L	L
Н	L	Н	Н
Н	Н	L	L
Н	Н	Н	Н



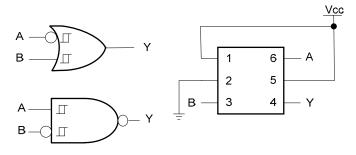
### **Logic Configurations**



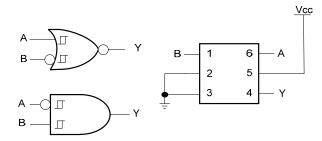
Configuration 1
2 to 1 Data Selector



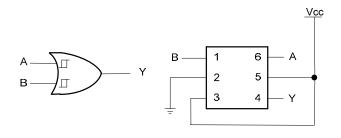
Configuration 2 2-Input AND Gate 2-Input NOR Gate with Both Inputs Inverted



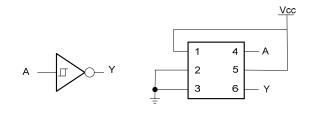
Configuration 3
2-Input NAND Gate with B Input Inverted
2-Input OR Gate with A Input Inverted



Configuration 4 2-Input NOR Gate with One Input Inverted 2-Input AND Gate with One Input Inverted



Configuration 5 2-Input OR Gate



Configuration 6 Inverter

Function Selection Table							
Logic Function	Configuration						
2-to-1 Data Selector	1						
2-input AND gate	2						
2-input AND with inverted input	3,4						
2-input NOR with inverted input	3,4						
2-input OR	5						
2-input NOR with both inputs inverted	2						
1-input Inverter	6						



### **Absolute Maximum Ratings (Note 2)**

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
Vı	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I <sub>OFF</sub> state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> <0	-50	mA
I <sub>OK</sub>	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

## **Recommended Operating Conditions (Note 3)**

Symbol		Parameter	Min	Max	Unit
\/	Operating Voltage	Operating	1.65	5.5	V
V <sub>CC</sub>	Operating Voltage	Data retention only	1.5		V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	Vcc	V
		V <sub>CC</sub> = 1.65 V		-4	
		V <sub>CC</sub> = 2.3 V		-8	
I <sub>OH</sub>	High-level output current	V 0.V		-16	mA
		$V_{CC} = 3 V$		-24	
		V <sub>CC</sub> = 4.5 V		-32	
		V <sub>CC</sub> = 1.65 V		4	
		V <sub>CC</sub> = 2.3 V		8	
I <sub>OL</sub>	Low-level output current	V 0V		16	mA
		$V_{CC} = 3 V$		24	
		V <sub>CC</sub> = 4.5 V		32	
		V <sub>CC</sub> = 1.8 V ± 0.15V, 2.5 V ± 0.2 V		20	
Δt/ΔV	Input transition rise or fall rate	Input transition rise or fall $V_{co} = 3.3 \text{ V} + 0.3 \text{ V}$		10	ns/V
	late	V <sub>CC</sub> = 5 V ± 0.5 V		5	
T <sub>A</sub>	Operating free-air temperature		-40	125	°C

Notes: 3. Unused inputs should be held at Vcc or Ground.



# Electrical Characteristics $T_A = -40$ °C to 85 °C (All typical values are at Vcc = 3.3V, $T_A = 25$ °C)

Symbol	Parameter	Test Conditions	V <sub>cc</sub>	Min	Тур.	Max	Unit	
			1.65 V	0.70		1.20		
			2.3V	1.11		1.60		
$V_{T+}$	Positive-going input threshold voltage		3 V	1.50		2.00		
	tinoonola voltago		4.5 V	2.16		2.74		
			5.5 V	2.61		3.33		
			1.65 V	0.30		0.72		
			2.3V	0.58		1.00		
$V_{T-}$	Negative-going input threshold voltage		3 V	0.80		1.30		
	in contoid voltage		4.5 V	1.21		1.95		
			5.5 V	1.45		2.35		
			1.65 V	0.30		0.62		
			2.3V	0.40		0.80		
$\Delta V_{T}$	Hysteresis $(V_{T+} - V_{T-})$		3 V	0.35		1.00		
			4.5 V	0.55		1.10		
			5.5 V	0.60		1.20		
	High Level Output Voltage	I <sub>OH</sub> = -100μA	1.65 V to 5.5V	V <sub>CC</sub> - 0.1				
		I <sub>OH</sub> = -4mA	1.65 V	1.2				
V		I <sub>OH</sub> = -8mA	2.3V	1.9			V	
$V_{OH}$		I <sub>OH</sub> = -16mA	2.1/	2.4			- V	
		I <sub>OH</sub> = -24mA	3 V	2.3				
		I <sub>OH</sub> = -32mA	4.5 V	3.8				
		$I_{OL} = 100 \mu A$	1.65 V to 5.5V			0.1		
		I <sub>OL</sub> = 4mA	1.65 V			0.45		
\ /	High lavel lagest Valtage	I <sub>OL</sub> = 8mA	2.3V			0.3	.,	
$V_{OL}$	High-level Input Voltage	I <sub>OL</sub> = 16mA	2.1/			0.4	V	
		I <sub>OL</sub> = 24mA	3 V			0.55		
		$I_{OL} = 32mA$	4.5			0.55		
I <sub>I</sub>	Input Current	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			± 5	μA	
l <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 5.5V$	0			± 10	μA	
I <sub>cc</sub>	Supply Current	$V_I = 5.5V$ of GND $I_O=0$	1.65 V to 5.5V			10	μA	
Δl <sub>CC</sub>	Additional Supply Current	One input at V <sub>CC</sub> –0.6 V Other inputs at V <sub>CC</sub> or GND	3 V to 5.5V			500	μA	



# Electrical Characteristics $T_A = -40 \, ^{\circ}\text{C}$ to 125 $^{\circ}\text{C}$ (All typical values are at Vcc = 3.3V, $T_A = 25 \, ^{\circ}\text{C}$ )

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit
			1.65 V	0.70		1.20	
			2.3V	1.11		1.60	
$V_{T+}$	Positive-going input threshold voltage		3 V	1.50		2.00	
	tillesiloid voltage		4.5 V	2.16		2.74	
			5.5 V	2.61		3.33	
			1.65 V	0.30		0.75	
			2.3V	0.58		1.03	
$V_{T-}$	Negative-going input threshold voltage		3 V	0.80		1.33	
	tineshold voltage		4.5 V	1.21		1.95	
			5.5 V	1.45		2.35	
			1.65 V	0.30		0.62	
	Hysteresis (V <sub>T+</sub> - V <sub>T-)</sub>		2.3V	0.37		0.80	
$\Delta V_T$			3 V	0.32		1.00	
			4.5 V	0.50		1.20	
			5.5 V	0.55		1.40	
	High Level Output Voltage	I <sub>OH</sub> = -100μA	1.65 V to 5.5V	V <sub>CC</sub> - 0.1			
		$I_{OH} = -4mA$	1.65 V	0.95			
		$I_{OH} = -8mA$	2.3V	1.7			ļ ,,
$V_{OH}$		I <sub>OH</sub> = -16mA	0.14	1.9			V
		I <sub>OH</sub> = -24mA	3 V	2.0			
		I <sub>OH</sub> = -32mA	4.5 V	3.4			
		I <sub>OL</sub> = 100μA	1.65 V to 5.5V			0.1	
		I <sub>OL</sub> = 4mA	1.65 V			0.7	
\	I Bala Jawa Hamat Maltana	I <sub>OL</sub> = 8mA	2.3V			0.45	\ ,,
$V_{OL}$	High-level Input Voltage	I <sub>OL</sub> = 16mA	0.14			0.6	V
		I <sub>OL</sub> = 24mA	3 V			0.8	
		I <sub>OL</sub> = 32mA	4.5			0.8	
I <sub>I</sub>	Input Current	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			± 100	μA
l <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 5.5V$	0			± 200	μΑ
I <sub>CC</sub>	Supply Current	$V_I = 5.5V$ of GND $I_O=0$	1.65 V to 5.5V			200	μΑ
$\Delta I_{CC}$	Additional Supply Current	One input at V <sub>CC</sub> –0.6 V Other inputs at V <sub>CC</sub> or GND	3 V to 5.5V			5000	μΑ



## Electrical Characteristics (All typical values are at Vcc = 3.3V, T<sub>A</sub> = 25°C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit
C <sub>i</sub>	Input Capacitance	$V_i = V_{CC} - \text{or GND}$	3.3		3.5		pF
		SOT26	(Note 4)		166		
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	SOT363	(Note 4)		333		°C/W
		DFN1010	(Note 4)		231		
		SOT26	(Note 4)		46		
$\theta_{JC}$	Thermal Resistance Junction-to-Case	SOT363	(Note 4)		102		°C/W
		DFN1010	(Note 4)		TBD		

Notes: 4. Test condition for SOT26, SOT363 and DFN1010 : Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

### **Switching Characteristics**

 $T_A$ =-40 °C to 85 °C, CL = 30 or 50pF as noted (see Figure 1)

Parameter	From (Input)	TO (OUTPUT)	Vcc = 1.8 V         Vcc = 2.5 V         Vcc = 3.3 V           ± 0.15V         ± 0.2V         ± 0.3V		$\pm 0.15V$ $\pm 0.2V$ $\pm 0.3V$ $\pm 0.5V$			_	Unit		
	(input)	(001701)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Y	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

#### $T_A$ =-40 °C to 125 °C, CL = 30 or 50pF as noted (see Figure 1)

Parameter	From	TO (OUTPUT)	Vcc = 1.8 V ± 0.15V		Vcc = 2.5 V ± 0.2V		Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V		Unit
	(Input)	(001701)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Υ	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

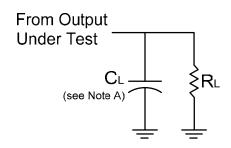
### **Operating Characteristics**

 $T_A = 25$  °C

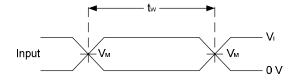
	Parameter		Test Conditions	Vcc = 1.8 V	Vcc = 2.5 V	Vcc = 3.3 V	Vcc = 5 V	Unit
١		i didilicici	Conditions	TYP	TYP	TYP	TYP	
	$C_{pd}$	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF



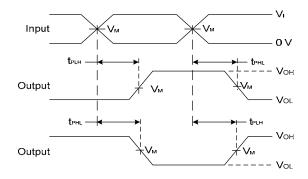
#### **Parameter Measurement Information**



Vcc	In	outs	V <sub>M</sub>	C <sub>L</sub>	R <sub>L</sub>
	VI	t <sub>r</sub> /t <sub>f</sub>			
1.8V±0.15V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1ΚΩ
2.5V±0.2V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	Vcc	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω



Voltage Waveform Pulse Duration



Voltage Waveform
Propagation Delay Times
Inverting and Non Inverting Outputs

Notes:

- A. Includes test lead and test apparatus capacitance.
- B. All pulses are supplied at pulse repetition rate  $\leq$  10 MHz
- C. Inputs are measured separately one transition per measurement
- D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD}$

Figure 1. Load Circuit and Voltage Waveforms



### **CONFIGURABLE MULTIPLE-FUNCTION GATE**

### **Ordering Information**

T4LVC1G 97 XXX - 7

Logic Device Function Package Packing

74 : Logic Prefix 97 : 3-Input W6 : SOT26 7 : Tape & Reel

LVC : 1.65 to 5.5V Configurable DW : SOT363 Family Multiple-Function FW4 : DFN1010

1G : One gate Gate

Device	Package Code	Packaging (Note 7)	7" Tape and Reel	
			Quantity	Part Number Suffix
74LVC1G97W6-7	W6	SOT26	3000/Tape & Reel	-7
74LVC1G97DW-7	DW	SOT363	3000/Tape & Reel	-7
74LVC1G97FW4-7	FW4	DFN1010	5000/Tape & Reel	-7

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

### **Marking Information**

#### (1) SOT26, SOT363

6 5 4 **XX Y W X**•
1 2 3

XX: Identification code

Y: Year 0~9

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal Code

Part Number	Package	Identification Code
74LVC1G97W6	SOT26	TY
74LVC1G97DW	SOT363	TY



### **Marking Information (Continued)**

#### (2) DFN1010

### (Top View)

XX  $\frac{XX}{Y}$ : Identification Code  $\frac{X}{Y}$ : Year : 0~9

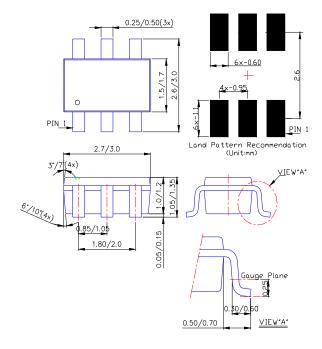
\overline{\tilde{W}}: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal code

Part Number	Package	Identification Code
74LVC1G97FW4	DFN1010	TY

### Package Outline Dimensions (All Dimensions in mm)

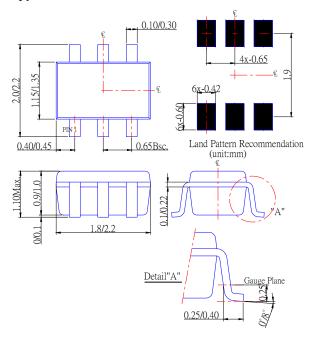
#### (1) Package Type: SOT26



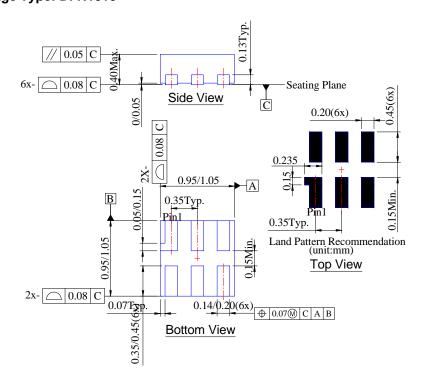


### Package Outline Dimensions (All Dimensions in mm) (Continued)

#### (2) Package Type: SOT363



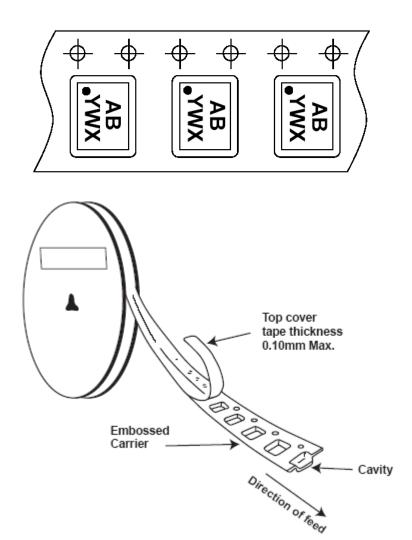
#### (3) Package Type: DFN1010





### **Taping Orientation (Note 8)**

#### For DFN1010



Notes: 8. The taping orientation of the other package type can be found on our website at http://www.diodes.com/datasheets/ap02007.pdf



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  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
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